$In_2Si[PO_4]_3O_{0.5}$	*hP*50	(176) $P6_3/m$ – i^2h^3fe

$In_4Si_2P_6O_{25}$ [1]
Structural features: InO_6 octahedra share vertices with PO_4 and SiO_4 tetrahedra (statistical occupation of two face-linked tetrahedra for the latter) to form a 3D-framework.

Hanawa M. et al. (2000) [1]
$In_2O_{12.50}P_3Si$
a = 0.85149, c = 0.77481 nm, c/a = 0.910, V = 0.4865 nm^3, Z = 2

site	Wyck.	sym.	*x*	*y*	*z*	occ.	atomic environment
O1	12*i*	1	0.0	0.022	0.0	0.083	
O2	12*i*	1	0.4381	0.1427	0.0864		single atom P
O3	6*h*	*m*..	0.0366	0.1923	$^1/_4$		
O4	6*h*	*m*..	0.1348	0.5163	$^1/_4$		single atom P
P5	6*h*	*m*..	0.36448	0.03735	$^1/_4$		tetrahedron O_4
In6	4*f*	3..	$^1/_3$	$^2/_3$	0.0436		octahedron O_6
Si7	4*e*	3..	0	0	0.2033	0.5	

Transformation from published data: *y*,*x*,-*z*; origin shift 0 0 $^1/_2$
Experimental: single crystal, diffractometer, X-rays, R = 0.044, T = 296 K
Remarks: Short interatomic distances for partly occupied site(s).

References: [1] Hanawa M., Kobayashi T., Imoto H. (2000), Z. Anorg. Allg. Chem. 626, 216-222.